

TC74HC283AP, TC74HC283AF, TC74HC283AFN

(Note) The JEDEC SOP (FN) is not available in Japan.

4 - BIT BINARY FULL ADDER

The TC74HC283A is a high speed CMOS 4 - BIT BINARY FULL ADDER fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

Sum (Σ) outputs are provided for each bit and a resultant carry (C4) is obtained from the fourth bit.

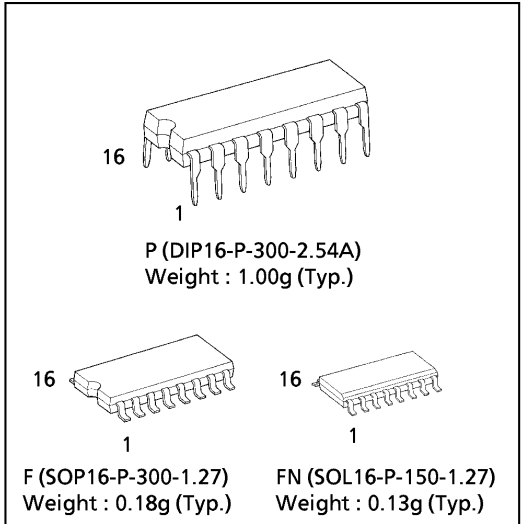
This adder features full internal look - ahead across all four bits.

A4 \times n bit binary adder is easily built up by cascading the HC283A without any additional logic.

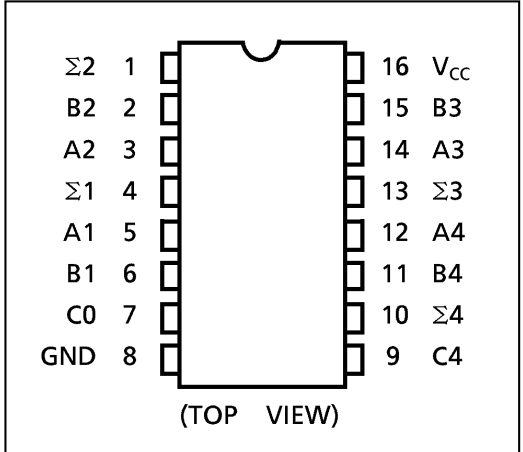
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES :

- High Speed..... $t_{pd} = 17ns$ (typ.) at $V_{CC} = 5V$
- Low Power Dissipation..... $I_{CC} = 4\mu A$ (Max.) at $T_a = 25^\circ C$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Output Drive Capability 10 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 4mA$ (Min.)
- Balanced Propagation Delays..... $t_{PLH} \approx t_{PHL}$
- Wide Operating Voltage Range... V_{CC} (opr.) = 2V~6V
- Pin and Function Compatible with 74LS283



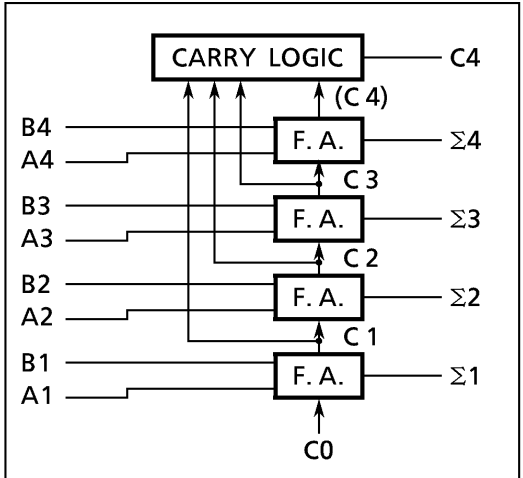
PIN ASSIGNMENT



TRUTH TABLE (1bit)

INPUTS			OUTPUTS	
B _n	A _n	C _{n-1}	Σ_n	C _n
L	L	L	L	L
L	L	H	H	L
L	H	L	H	L
L	H	H	L	H
H	L	L	H	L
H	L	H	L	H
H	H	L	L	H
H	H	H	H	H

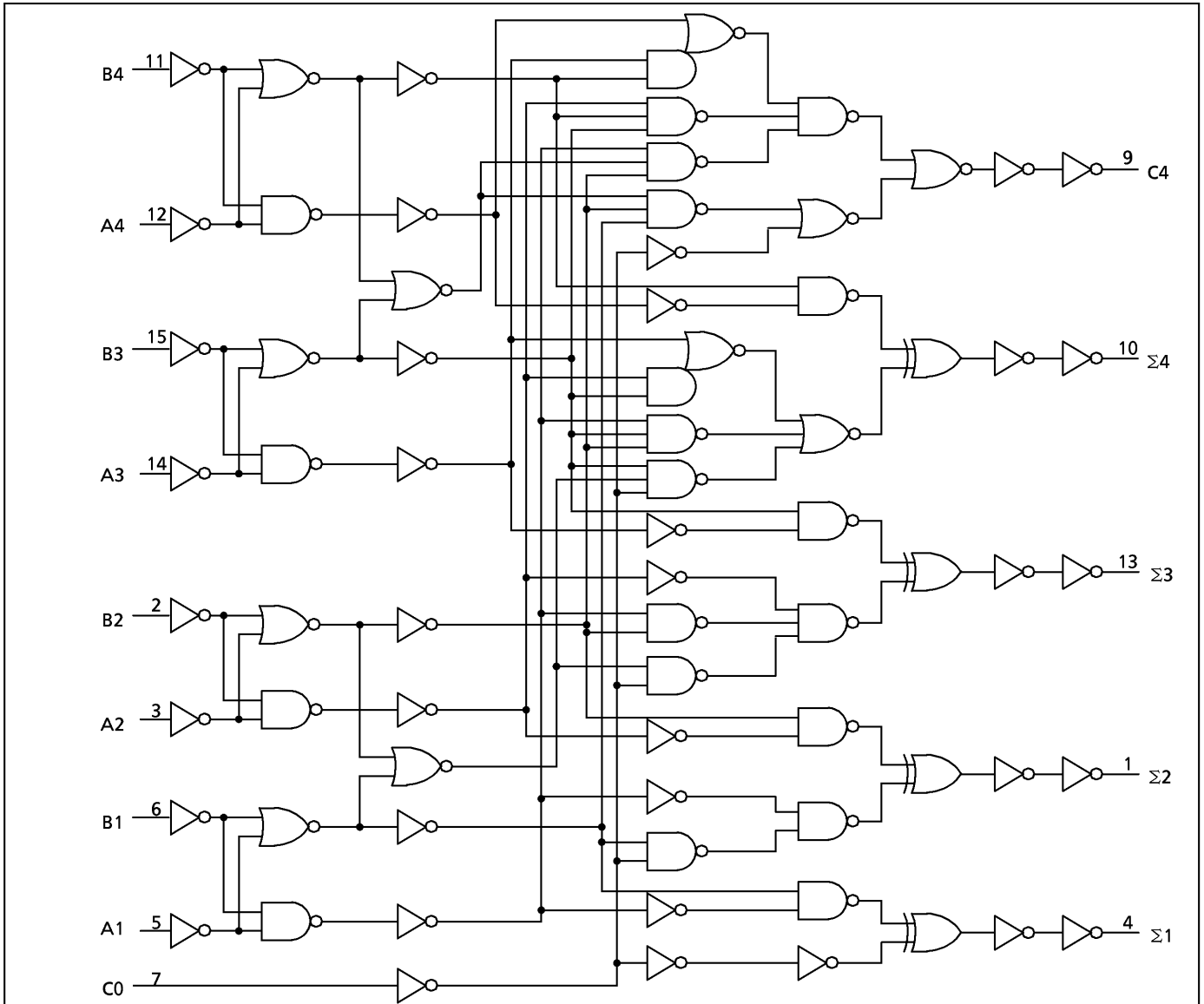
BLOCK DIAGRAM



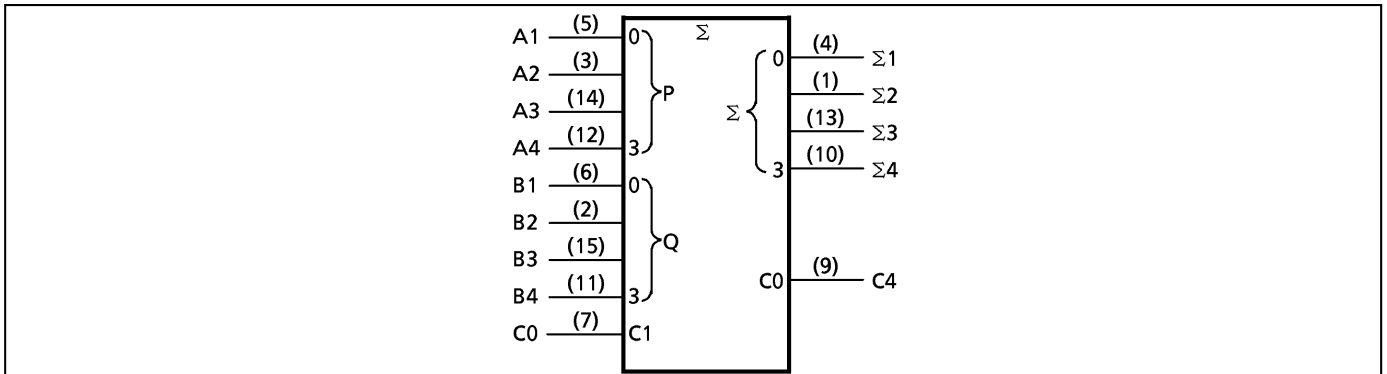
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SYSTEM DIAGRAM



IEC LOGIC SYMBOL



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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} /Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~ 1000 ($V_{CC} = 2.0\text{V}$) 0~ 500 ($V_{CC} = 4.5\text{V}$) 0~ 400 ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	$T_a = 25^{\circ}\text{C}$			$T_a = -40 \sim 85^{\circ}\text{C}$		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
High - Level Input Voltage	V_{IH}		2.0	1.50	—	—	1.50	—	V	
			4.5	3.15	—	—	3.15	—		
			6.0	4.20	—	—	4.20	—		
Low - Level Input Voltage	V_{IL}		2.0	—	—	0.50	—	0.50	V	
			4.5	—	—	1.35	—	1.35		
			6.0	—	—	1.80	—	1.80		
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	—	1.9	—	V
				4.5	4.4	4.5	—	4.4	—	
			6.0	5.9	6.0	—	5.9	—		
			$I_{OH} = -4\text{ mA}$ $I_{OH} = -5.2\text{ mA}$	4.5	4.18	4.31	—	4.13	—	
				6.0	5.68	5.80	—	5.63	—	
			Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	2.0	—	0.0	
4.5	—	0.0					0.1	—	0.1	
6.0	—	0.0				0.1	—	0.1		
$I_{OL} = 4\text{ mA}$ $I_{OL} = 5.2\text{ mA}$	4.5	—				0.17	0.26	—	0.33	
	6.0	—				0.18	0.26	—	0.33	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND				6.0	—	—	± 0.1	—
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	4.0	—	40.0		

AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH} t_{THL}		—	4	8	ns
Propagation Delay Time ($C0 - \Sigma n$)	t_{pLH} t_{pHL}		—	17	26	
Propagation Delay Time ($C0 - C4$)	t_{pLH} t_{pHL}		—	17	26	
Propagation Delay Time ($A_n, B_n - \Sigma n$)	t_{pLH} t_{pHL}		—	23	37	
Propagation Delay Time ($A_n, B_n - C4$)	t_{pLH} t_{pHL}		—	21	34	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	$T_a = 25^\circ\text{C}$			$T_a = -40\text{--}85^\circ\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{TLH} t_{THL}		2.0	—	30	75	—	95	ns
			4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Propagation Delay Time ($C0 - \Sigma n$)	t_{pLH} t_{pHL}		2.0	—	60	150	—	190	
			4.5	—	20	30	—	38	
			6.0	—	17	26	—	32	
Propagation Delay Time ($C0 - C4$)	t_{pLH} t_{pHL}		2.0	—	60	150	—	190	
			4.5	—	20	30	—	38	
			6.0	—	17	26	—	32	
Propagation Delay Time ($A_n, B_n - \Sigma n$)	t_{pLH} t_{pHL}		2.0	—	95	210	—	265	
			4.5	—	27	42	—	53	
			6.0	—	22	36	—	45	
Propagation Delay Time ($A_n, B_n - C4$)	t_{pLH} t_{pHL}		2.0	—	80	195	—	245	
			4.5	—	25	39	—	49	
			6.0	—	20	33	—	42	
Input Capacitance	C_{IN}			—	5	10	—	10	pF
Power Dissipation Capacitance	$C_{PD} (1)$			—	126	—	—	—	

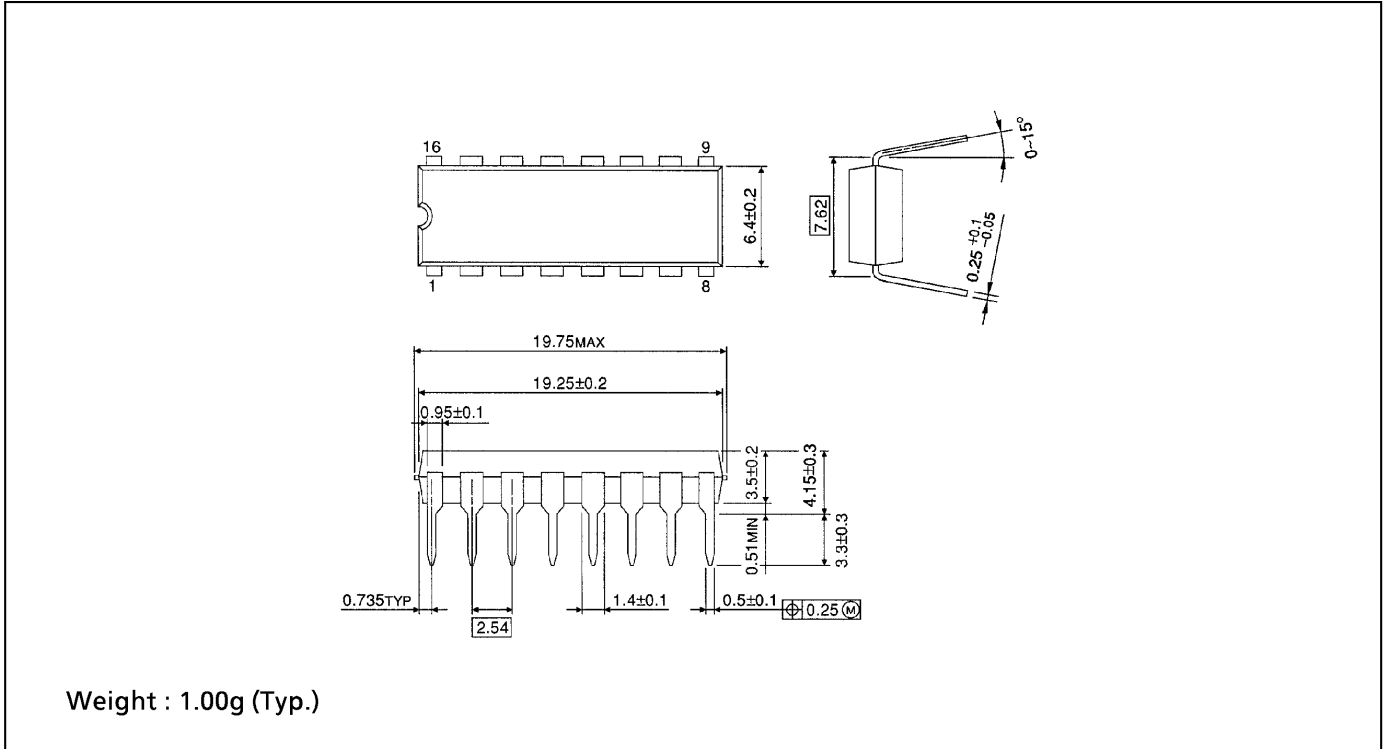
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

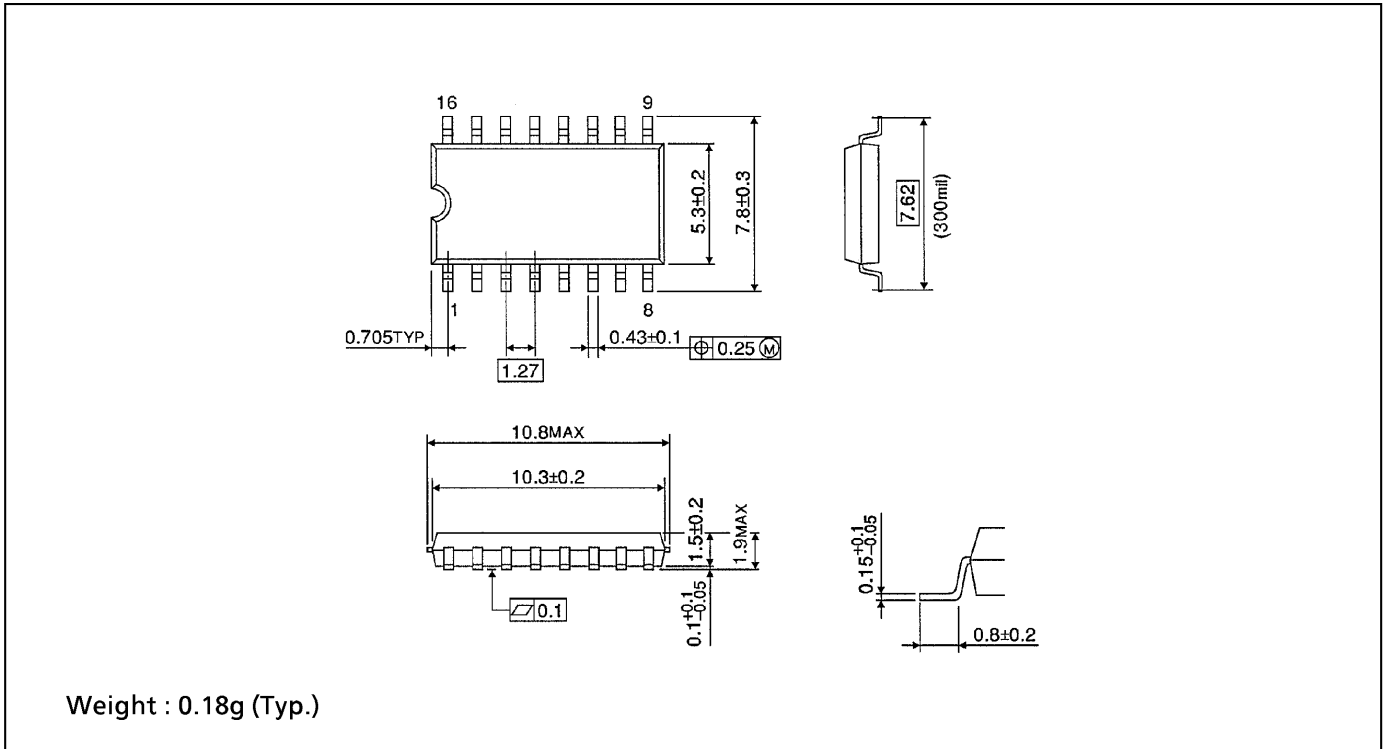
DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)

Unit in mm



SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

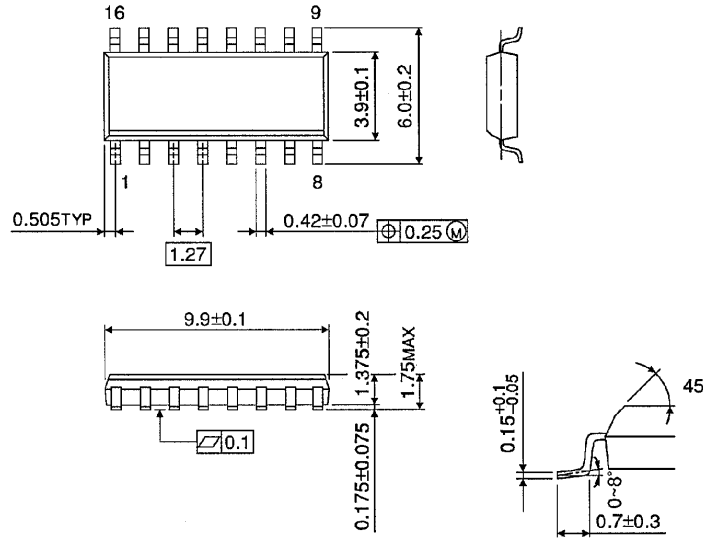
Unit in mm



SOP 16PIN (150mil BODY) OUTLINE DRAWING (SOL16-P-150 -1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.13g (Typ.)